1. General description

NPN/PNP general-purpose transistor pair in a very small SOT363 (SC-88) Surface-Mounted Povice (SMD) plactic package

Device (SMD) plastic package.

NPN/NPN complement: BC846BS-Q PNP/PNP complement: BC856BS-Q

2. Features and benefits

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- · Reduces number of components and board space
- No mutual interference between the transistors
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

· General-purpose switching and amplification

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor;	Per transistor; for the PNP transistor with negative polarity							
V _{CEO}	collector-emitter voltage	open base		-	-	65	V	
I _C	collector current			-	-	100	mA	
TR1 (NPN)							'	
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C		200	300	450		
TR2 (PNP)								
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		200	290	450		



65 V, 100 mA NPN/PNP general-purpose transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	П6 П5 П4	C1 B2 E2
2	B1	base TR1	6 5 4	
3	C2	collector TR2		(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	☐1 ☐2 ☐3	
6	C1	collector TR1	TSSOP6 (SOT363)	sym019

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
BC846BPN-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
BC846BPN-Q	PJ%

[1] % = placeholder for manufacturing site code

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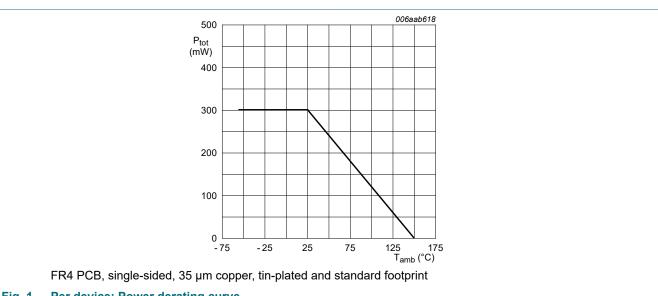
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or; for the PNP transistor wit	h negative polarity	,			
V _{CBO}	collector-base voltage	open emitter		-	80	V
V_{CEO}	collector-emitter voltage	open base		-	65	V
V_{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	200	mA
I _{BM}	peak base current			-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	200	mW
Per device					•	'
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



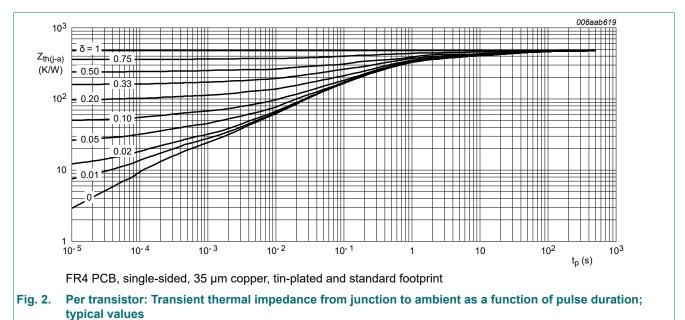
65 V, 100 mA NPN/PNP general-purpose transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	er transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	230	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



10. Characteristics

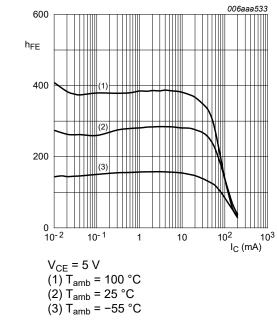
Table 7. Characteristics

Symbol	Parameter	Conditions	Mi	1 Тур	Max	Unit
TR1 (NPN)	,			'		
I _{CBO}	collector-base cut-off	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	15	nA
	current	V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 6 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 10 μA; T _{amb} = 25 °C	-	280	-	
		V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C	200	300	450	
V _{CEsat}	collector-emitter	I _C = 10 mA; I _B = 0.5 mA; T _{amb} = 25 °C	-	55	100	mV
	saturation voltage	I _C = 100 mA; I _B = 5 mA; T _{amb} = 25 °C	-	200	300	mV
V _{BEsat}		I _C = 10 mA; I _B = 0.5 mA; T _{amb} = 25 °C	-	755	850	mV
	voltage	I _C = 100 mA; I _B = 5 mA; T _{amb} = 25 °C	-	1000	-	mV

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BE}	base-emitter voltage	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C	580	650	700	mV
		V _{CE} = 5 V; I _C = 10 mA; T _{amb} = 25 °C	-	-	770	mV
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	1.9	-	pF
C _e	emitter capacitance	V _{EB} = 0.5 V; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	11	-	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz; T _{amb} = 25 °C	100	-	-	MHz
NF	noise figure	V_{CE} = 5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; f = 15.7 kHz; T_{amb} = 25 °C	-	1.9	-	dB
		V_{CE} = 5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; f = 1 kHz; B = 200 Hz; T_{amb} = 25 °C	-	3.1	-	dB
TR2 (PNP)					'	·
I _{CBO}	collector-base cut-off	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-15	nA
	current	V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C	-	-	-5	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -6 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -10 μA; T _{amb} = 25 °C	-	270	-	
		V _{CE} = -5 V; I _C = -2 mA; T _{amb} = 25 °C	200	290	450	
V _{CEsat}	collector-emitter	I _C = -10 mA; I _B = -0.5 mA; T _{amb} = 25 °C	-	-55	-100	mV
	saturation voltage	I _C = -100 mA; I _B = -5 mA; T _{amb} = 25 °C	-	-200	-300	mV
V _{BEsat}	base-emitter saturation	I _C = -10 mA; I _B = -0.5 mA; T _{amb} = 25 °C	-	-755	-850	mV
	voltage	I _C = -100 mA; I _B = -5 mA; T _{amb} = 25 °C	-	-900	-	mV
V _{BE}	base-emitter voltage	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	-600	-650	-750	mV
		V _{CE} = -5 V; I _C = -10 mA; T _{amb} = 25 °C	-	-	-820	mV
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	2.3	-	pF
C _e	emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; i_{c} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	10	-	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; f = 100 \text{ MHz};$ $T_{j} = 25 \text{ °C}$	100	-	-	MHz
NF	noise figure	V_{CE} = -5 V; I_{C} = -0.2 mA; R_{S} = 2 k Ω ; f = 15.7 kHz; T_{amb} = 25 °C	-	1.6	-	dB
		V_{CE} = -5 V; I_{C} = -0.2 mA; R_{S} = 2 k Ω ; f = 1 kHz; B = 200 Hz; T_{amb} = 25 °C	-	2.9	-	dB

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TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values

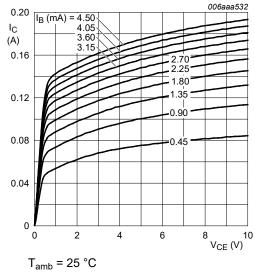


Fig. 4. TR1 (NPN): Collector current as a function of collector-emitter voltage; typical values

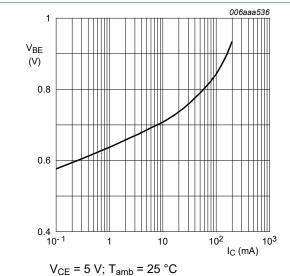
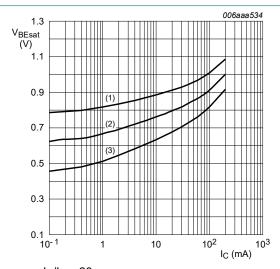


Fig. 5. TR1 (NPN): Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

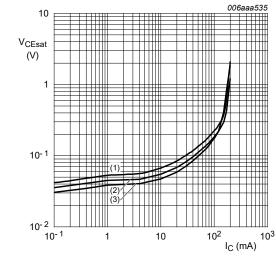
(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

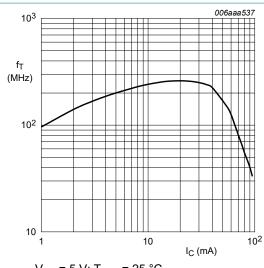
Fig. 6. TR1 (NPN): Base-emitter saturation voltage as a function of collector current; typical values

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I_C/I_B = 20 (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -55 °C

TR1 (NPN): Collector-emitter saturation voltage Fig. 7. as a function of collector current; typical values



 V_{CE} = 5 V; T_{amb} = 25 °C

TR1 (NPN): Transition frequency as a function Fig. 8. of collector current; typical values

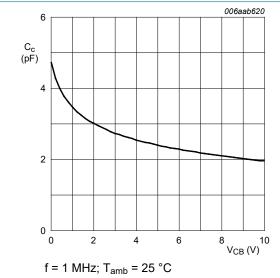
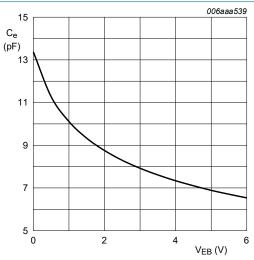


Fig. 9. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



f = 1 MHz; T_{amb} = 25 °C

Fig. 10. TR1 (NPN): Emitter capacitance as a function of emitter-base voltage; typical values

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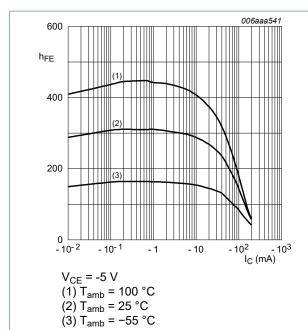


Fig. 11. TR2 (PNP): DC current gain as a function of collector current; typical values

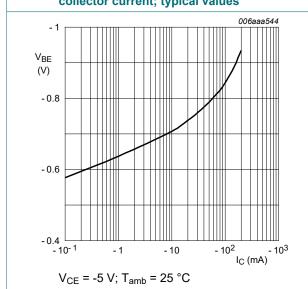


Fig. 13. TR2 (PNP): Base-emitter voltage as a function of collector current; typical values

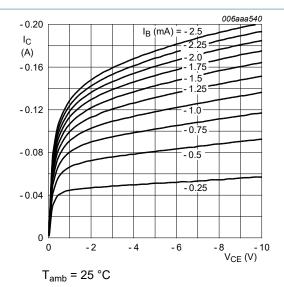
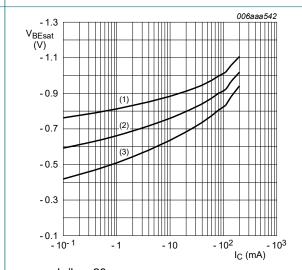


Fig. 12. TR2 (PNP): Collector current as a function of collector-emitter voltage; typical values

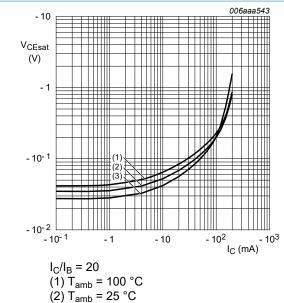


 $I_C/I_B = 20$ (1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 14. TR2 (PNP): Base-emitter saturation voltage as a function of collector current; typical values

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as a function of collector current; typical values

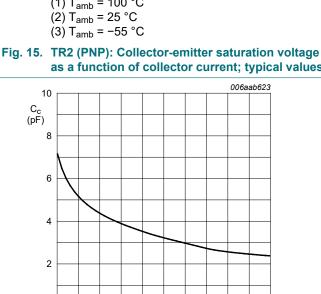


Fig. 17. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values

- 6

-8 -10 V_{CB} (V)

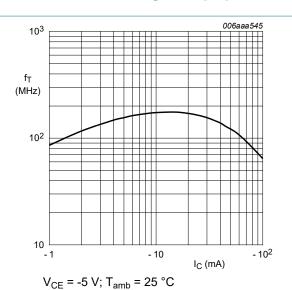


Fig. 16. TR2 (PNP): Transition frequency as a function of collector current; typical values

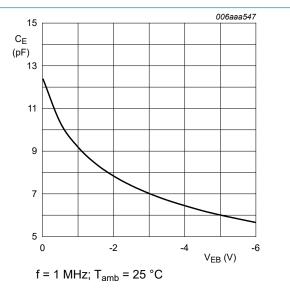


Fig. 18. TR2 (PNP): Emitter capacitance as a function of emitter-base voltage; typical values

11. Test information

- 2

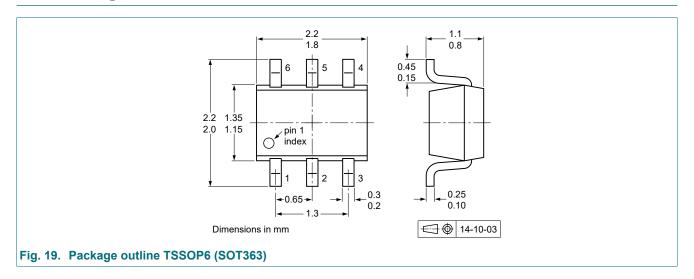
f = 1 MHz; T_{amb} = 25 °C

Quality information

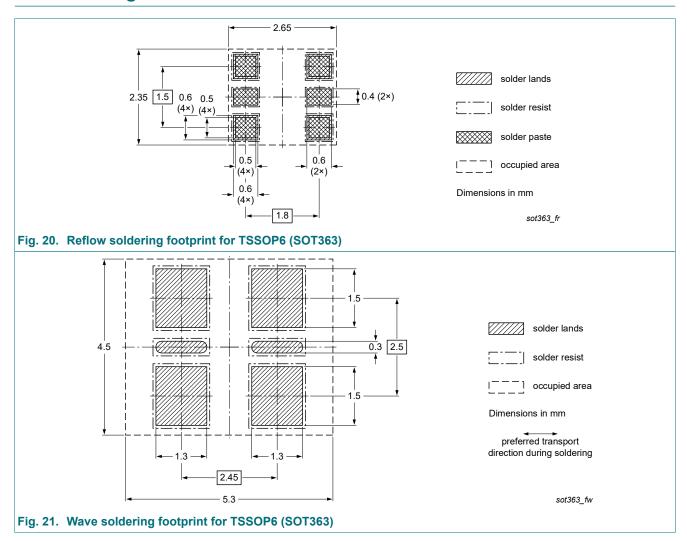
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC846BPN-Q v.1	20211209	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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